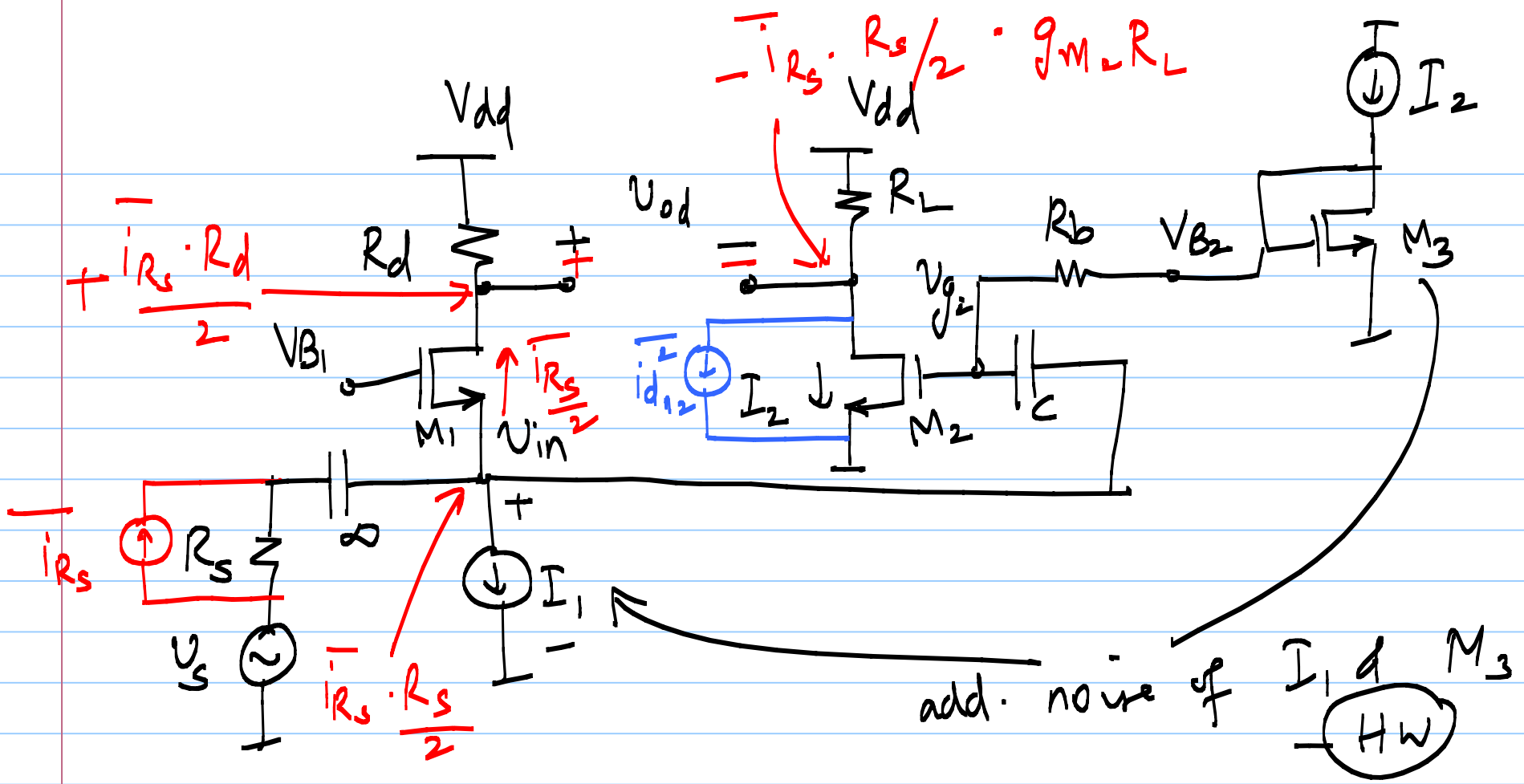


26/2/20

## Lec 18

$\overline{v_{odn}^2}$  for noise cancelling LNA:

- 1) Noise from  $M_1$  (CG stage) = 0
- 2) Noise from  $M_2$  (CS stage) =  $4kT \gamma g_{m2} \cdot R_L^2$
- 3) Noise from  $R_L$  =  $4kT R_L$
- 4) Noise from  $R_d$  =  $4kT R_d$
- 5) Noise from  $R_s$  =  $\left| \frac{\overline{i_{R_s}}}{2} (R_d + R_s g_{m2} R_L) \right|^2$   
 $= \left| \frac{\overline{i_{R_s}}}{2} (R_d + R_s \cdot \frac{R_d}{R_s}) \right|^2$   
 $= \left| \overline{i_{R_s}} \cdot R_d \right|^2 = \frac{4kT R_d^2}{R_s}$



$$NF = 1 + \frac{4kT\gamma g_{m2}R_L^2 + 4kTR_L + 4kTR_d}{4kT \cdot R_d^2/R_s}$$

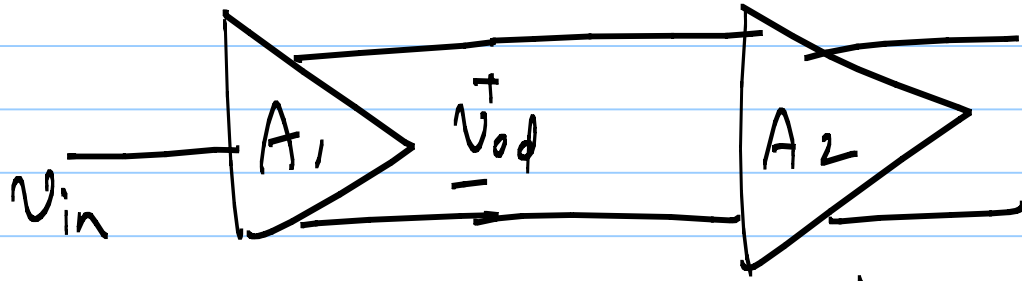
$$= 1 + \gamma \cdot \frac{(g_{m2}R_L)}{R_d/R_s} \cdot \left(\frac{R_L}{R_d}\right) + \frac{R_LR_s}{R_d^2} + \frac{R_s}{R_d}$$

$$NF = 1 + \gamma \cdot \frac{R_L}{R_d} + \frac{R_s}{R_d} + \frac{R_LR_s}{R_d^2}$$

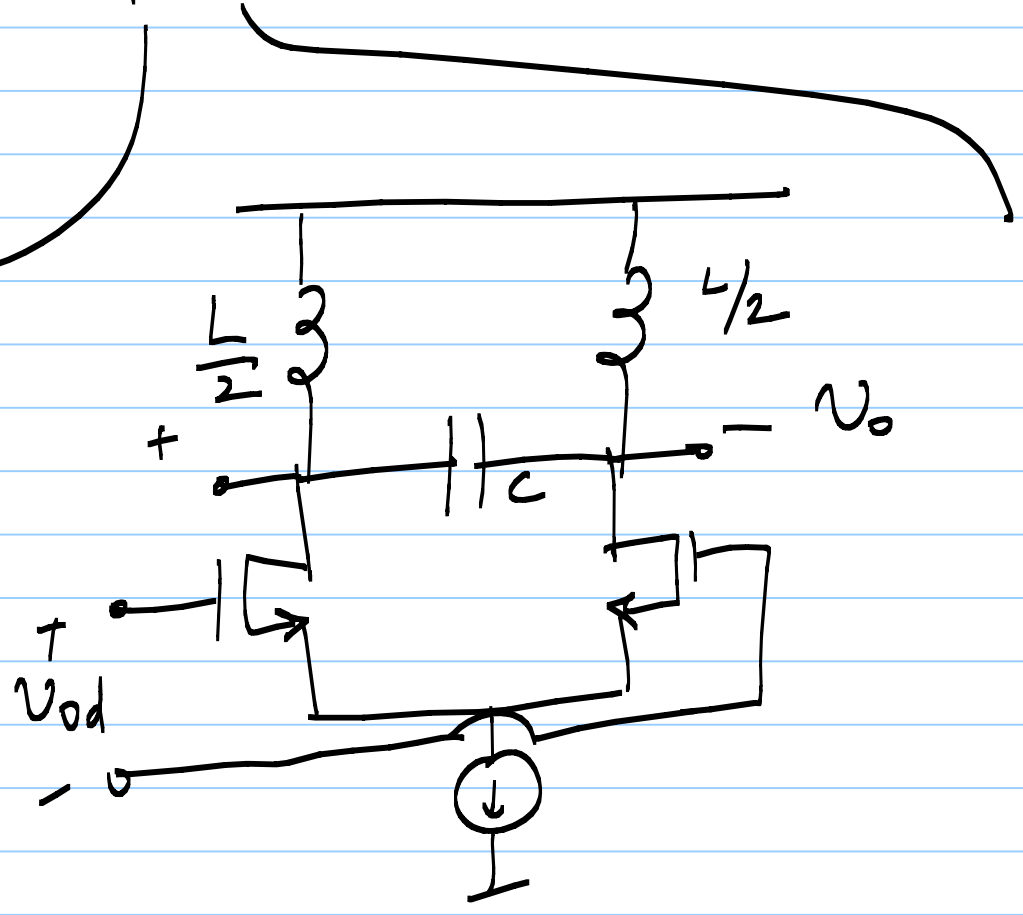
$$\frac{R_d}{R_s} = g_{m2} \cdot R_L$$

$$\frac{R_L}{R_d} = \frac{1}{g_{m2} R_s}$$

low NF  $\Rightarrow$  maximise  $R_d$ , minimise  $R_L$   
 $\Rightarrow$  maximise  $g_{m2}$



Noise  
cancelling  
LNA



11P<sub>3</sub> :

\* MOSFET with purely square law behaviour

$$I_D = \frac{1}{2} \mu_n C_{ox} \left( \frac{W}{L} \right) (V_{GS} - V_T)^2$$

$$11P_3 = \infty$$

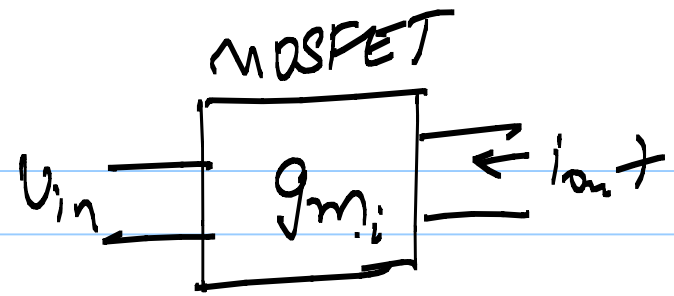
there is no 3<sup>rd</sup> order component  $a_3 = 0$

\* Cannot design for 11P<sub>3</sub>

\* Design for all other specs

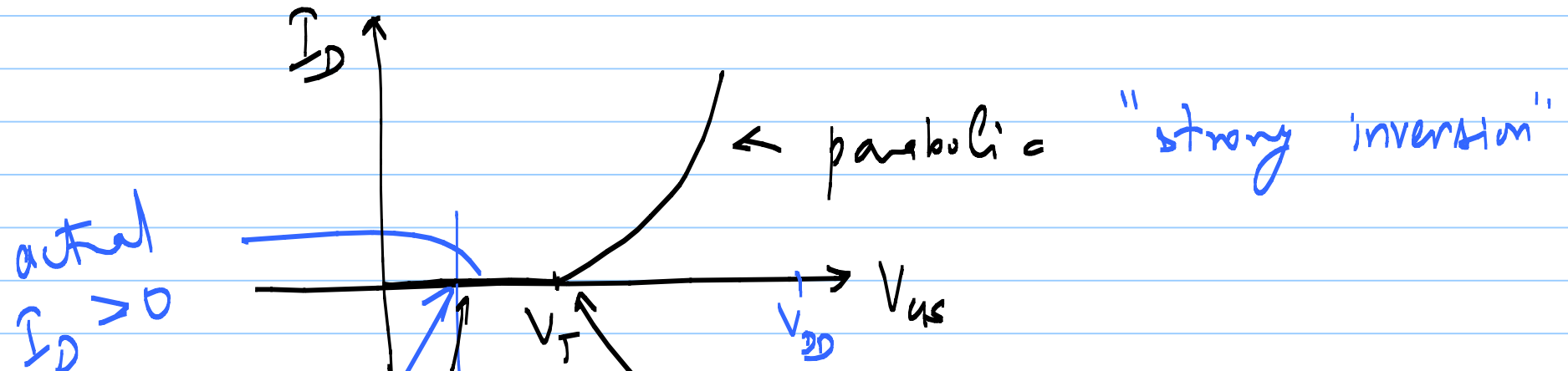
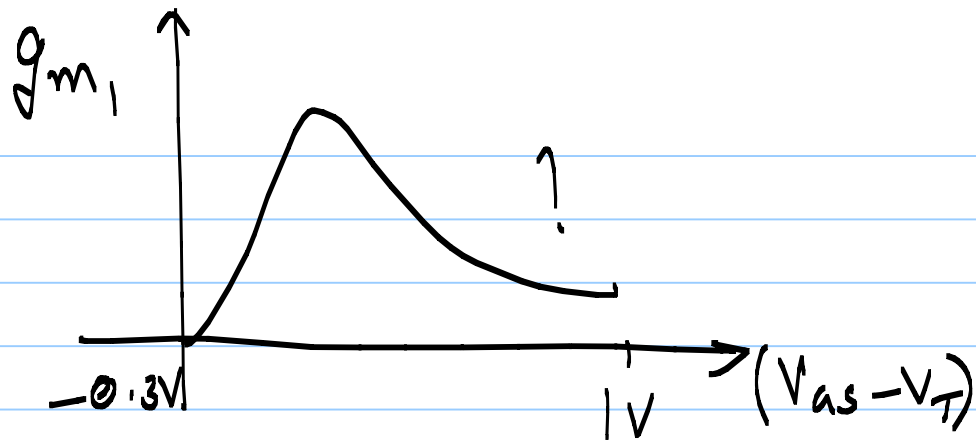
\* Then "measure" 11P<sub>3</sub>  
(simulate)

$$g_{m_1} = \frac{\partial I_D}{\partial V_{GS}} = \alpha_1$$



$$g_{m_2} = \frac{1}{2!} \frac{\partial^2 I_D}{\partial V_{GS}^2} = \alpha_2$$

$$g_{m_3} = \frac{1}{3!} \frac{\partial^3 I_D}{\partial V_{GS}^3} = \alpha_3$$



$V_{depl.}$   $\rightarrow$   $V_T$   $\rightarrow$   $V_{D0}$

@  $V_{as} = V_T$ , device inverts

$\hookrightarrow$  device goes from depletion  $\rightarrow$  weak inversion  $\rightarrow$  moderate inv.  $\rightarrow$  strong inv.

$I_D$  vs  $V_{as}$  is exponential



\* If  $V_{as} \sim V_T \Rightarrow$  moderate inv.

$\rightarrow$  device transitions from exp. to  $( )^2$

$$V_T - 0.1V < V_{as} < V_T + 0.1V$$

$$\downarrow (V_{as} - V_T) \propto \sqrt{\frac{I_D}{(W/L)}} \Rightarrow \begin{matrix} \uparrow (W/L) \\ \downarrow I_D \end{matrix} \left. \vphantom{\begin{matrix} \uparrow (W/L) \\ \downarrow I_D \end{matrix}} \right\} \begin{matrix} \text{very} \\ \text{low } f_T \end{matrix}$$

weak inv.  $I_D = I_0 \exp\left(\frac{V_{as} - V_T}{\eta V_T}\right)$  "sub-threshold" operation

\*  $I I_B \neq \infty$  in subthreshold region